Product data sheet

1. General description

AC Thyristor Triac power switch in a SOT404 (D2PAK) surface mountable plastic package with self-protective clamping capabilities against low and high energy transients.

2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- · High minimum I_{GT} for guaranteed immunity to gate noise
- · Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- · Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- · Less sensitive gate for high noise immunity
- Surface mountable package
- · Triggering in three quadrants only
- · Very high immunity to false turn-on by dV/dt

3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- · Large and small appliances (White Goods)
- Reversing induction motor controls

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 105 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	-	8	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	80	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	-	88	Α
Tj	junction temperature		-	-	125	°C
V _{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; Fig. 6	-	-	2	kV

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G+;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 8}}{\text{C}}$	5	-	30	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 8}}{\text{C}}$	5	-	30	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$	5	-	30	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 10</u>	-	-	35	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 11</u>	-	1.3	1.5	V
V _{CL}	clamping voltage	I_{CL} = 0.1 mA; t_p = 1 ms; T_j = 25 °C	850	-	-	V
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; gate open circuit	2000	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 8 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	8	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	СМ	common	mb	LD -		
2	LD	load				
3	G	gate			<u> </u>	G—/
mb	LD	mounting base; load	D2PAK (SOT404)	CM 003aaf296		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
ACTT8B-800C0	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

7. Marking

Table 4. Marking codes

Type number	Marking code
ACTT8B-800C0	ACTT8B-800C0

8. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 105 ^{\circ}\text{C}$; $\overline{\text{Fig. 1}}$; $\overline{\text{Fig. 2}}$; $\overline{\text{Fig. 3}}$	-	8	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	80	A
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	88	Α
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	32	A²s
dl _T /dt	rate of rise of on-state current	I _G = 70 mA	-	100	A/µs
I _{GM}	peak gate current	t = 20 μs	-	2	Α
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C
V_{PP}	peak pulse voltage	T _i = 25 °C; non-repetitive, off-state; Fig. 6	-	2	kV

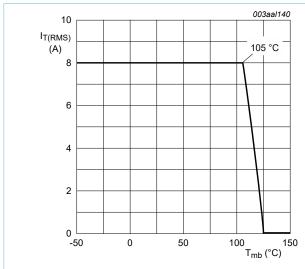
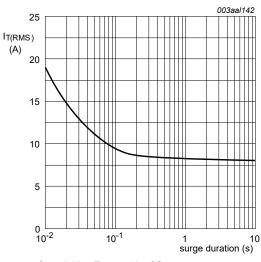


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} = 105 \text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

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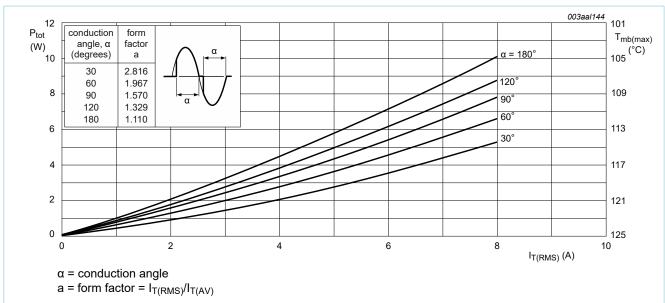


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

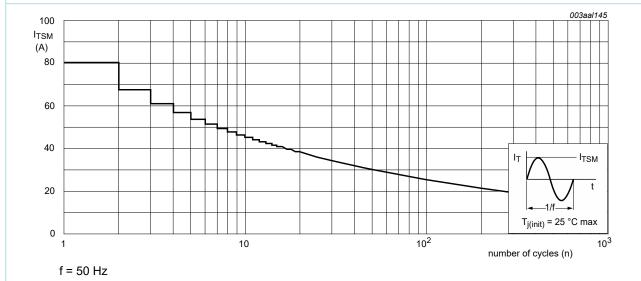


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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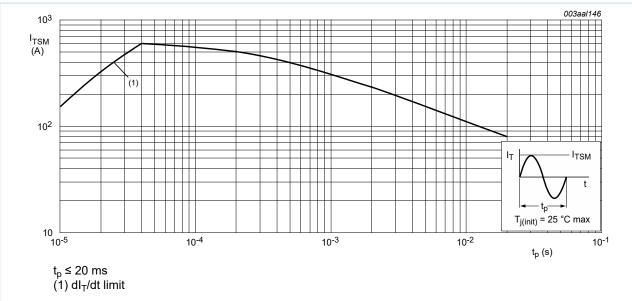


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

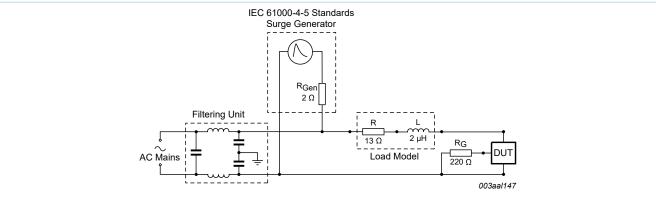
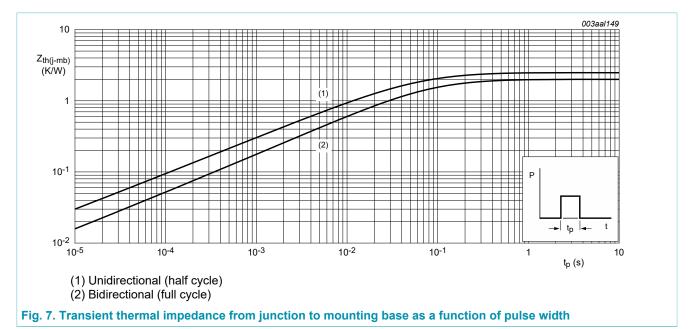


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; Fig. 7	-	-	2	K/W
	from junction to mounting base	half cycle; Fig. 7	-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air; printed circuit board (FR4) mounted	-	55	-	K/W



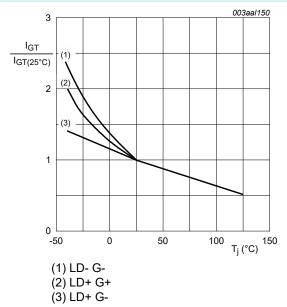
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		,			
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	5	-	30	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; Fig. 8}$	5	-	30	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$	5	-	30	mA
lL	latching current	$V_D = 12 \text{ V; } I_G = 100 \text{ mA; LD+ G+;}$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	50	mA
		$V_D = 12 \text{ V; } I_G = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	70	mA
		$V_D = 12 \text{ V; } I_G = 100 \text{ mA; LD- G-;}$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	50	mA
l _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 10</u>	-	-	35	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 11</u>	-	1.3	1.5	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 100 mA; T _j = 25 °C; Fig. 12	-	0.8	1	V
		V _D = 400 V; I _T = 100 mA; T _j = 125 °C; Fig. 12	0.2	0.45	-	V
l _D	off-state current	V _D = 800 V; T _j = 25 °C	-	-	10	μA
		V _D = 800 V; T _j = 125 °C	-	-	0.5	mA
V _{CL}	clamping voltage	$I_{CL} = 0.1 \text{ mA}; t_p = 1 \text{ ms}; T_j = 25 \text{ °C}$	850	-	-	V
Dynamic ch	naracteristics		1			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	2000	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}$; $T_j = 125 \text{ °C}$; $I_{T(RMS)} = 8 \text{ A}$; $dV_{com}/dt = 20 \text{ V/}\mu\text{s}$; (snubberless condition); gate open circuit	8	-	-	A/ms

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junction temperature

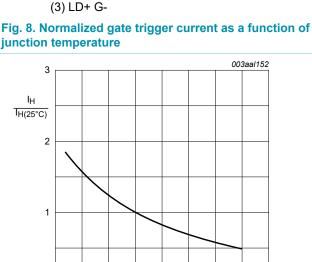


Fig. 10. Normalized holding current as a function of junction temperature

50

T_i (°C)

0

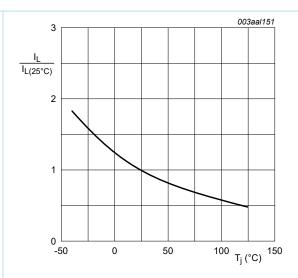
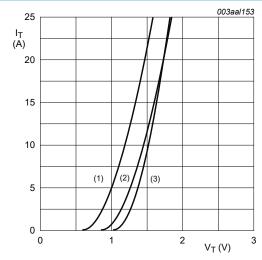


Fig. 9. Normalized latching current as a function of junction temperature

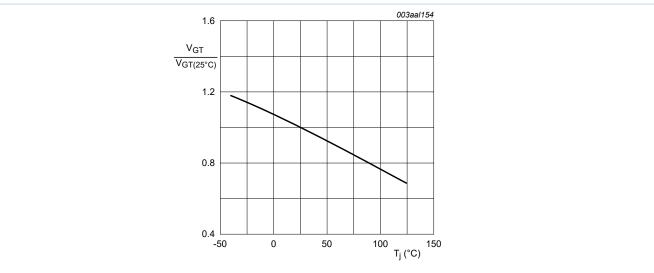


 V_o = 1.103 V; R_s = 0.034 Ω (1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values (3) T_j = 25 °C; maximum values

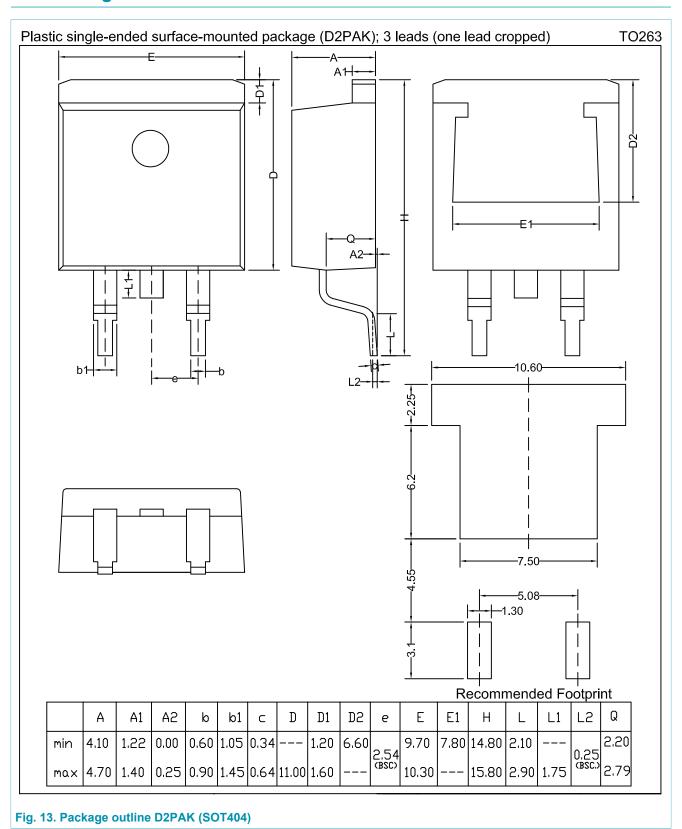
Fig. 11. On-state current as a function of on-state voltage

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AC Thyristor Triac power switch



11. Package outline



12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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